

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	MALINOWSKI-JOHN MALINOWSKI-JOHN-C MALINOWSKI-JOHN-CHESTER	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:59
L2	1146	(esd near1 discharg\$3 near1 (protection sensitive) near1 (circuit device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:04
L3	3087	(esd near1 (protection sensitive) near1 (circuit device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:33
L4	3087	2 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:05
L5	7	4 with ((spark adj gap) (field adj emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
L6	63	4 and ((spark adj gap) (field adj emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
L7	13	4 same ((spark adj gap) (field adj emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:07
L8	34	4 same ((spark near gap) (gated adj diod\$2) (field near emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:03

L9	5569	esd near1 (protection sensitive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:33
L10	1413	9 with ((spark near gap) diod\$2 (field near emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:35
L11	1022	10 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:35
L12	32	10 with substrate with (chip die ic (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 13:28
L13	2	("5877534" "6365932").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 10:43
L14	0	("6576506").URPN.	USPAT	OR	ON	2005/09/16 10:44
L15	373	10 with (chip die ic (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:05
L16	48	15 and ((substrate carrier) near4 (ceramic insulation dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:04
L17	13	("6198136").URPN.	USPAT	OR	ON	2005/09/16 13:39
L18	7	("20030089979" "5414299" "5866924" "5904499" "6046901" "6198136" "6303996").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 13:43
L19	12	("5970321").URPN.	USPAT	OR	ON	2005/09/16 14:01
L20	1	("6288885").URPN.	USPAT	OR	ON	2005/09/16 14:09

L21	7	("5287241" "5369552" "5784242" "5959821" "5970321" "5991135" "6060752").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 14:10
L22	74	12 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:29
L23	19	"6180426"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:30
L24	12	23 and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:30
L25	6	("5461333" "5481205" "5534465" "5731945" "5807791" "5818748").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 14:34
L26	4108	257/355-365.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:02
L27	1110	26 and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:02
L28	3549	esd with ((spark near gap) capacitor resistor diod\$2 (gated adj diod\$2) (field near emission))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:04
L29	679	26 and 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:04

L30	85	29 and ((substrate carrier) near4 (ceramic insulation dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:04
L31	81	30 and (chip die ic (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:05